ABSTRACT

There is provided a positive photoresist composition capable of forming a pattern with excellent resolution, excellent resistance to reflection off the substrate, and excellent perpendicularity. The positive photoresist composition comprises (A) an alkali-soluble novolak resin in which a portion of the hydrogen atoms of all the phenolic hydroxyl groups are substituted with 1,2-naphthoquinonediazidesulfonyl groups, and (B) a dissolution promoter represented by a general formula (b-1) and/or a general formula (b-11) shown below.

$$R^{2}$$
 R^{1}
 R^{5}
 R^{9}
 R^{10}
 R^{10}
 R^{10}
 R^{10}
 R^{11}
 R^{15}
 R^{13}
 R^{13}

5

10

$$(R^{42})_s$$
 $(H0)_p = (R^{41})_r$
 $(R^{43})_t$
 $(R^{43})_t$